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YAMANE et al.(10) **Pub. No.: US 2009/0160574 A1**(43) **Pub. Date: Jun. 25, 2009**(54) **BOUNDARY ACOUSTIC WAVE FILTER****Publication Classification**(75) Inventors: **Takashi YAMANE**, Yasu-shi (JP);
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CO., LTD., Nagaokakyo-shi (JP)(57) **ABSTRACT**(21) Appl. No.: **12/398,237**(22) Filed: **Mar. 5, 2009****Related U.S. Application Data**(63) Continuation of application No. PCT/JP2007/067322,
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A boundary acoustic wave filter device includes an electrode structure provided at a boundary between a piezoelectric body and a dielectric body laminated on the piezoelectric body and utilizes an SH-type boundary acoustic wave that propagates along the boundary. In the boundary acoustic wave filter device, the electrode structure includes a longitudinally coupled resonator boundary acoustic wave filter portion that has a first IDT and second and third IDTs arranged respectively on both sides of the IDT in a direction in which the boundary acoustic wave propagates. At portions at which two IDTs are located adjacent to each other in the direction in which the boundary acoustic wave propagates, narrow pitch electrode finger portions are provided in the IDTs, and the pitch of the electrode fingers of the narrow pitch electrode finger portion is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions.

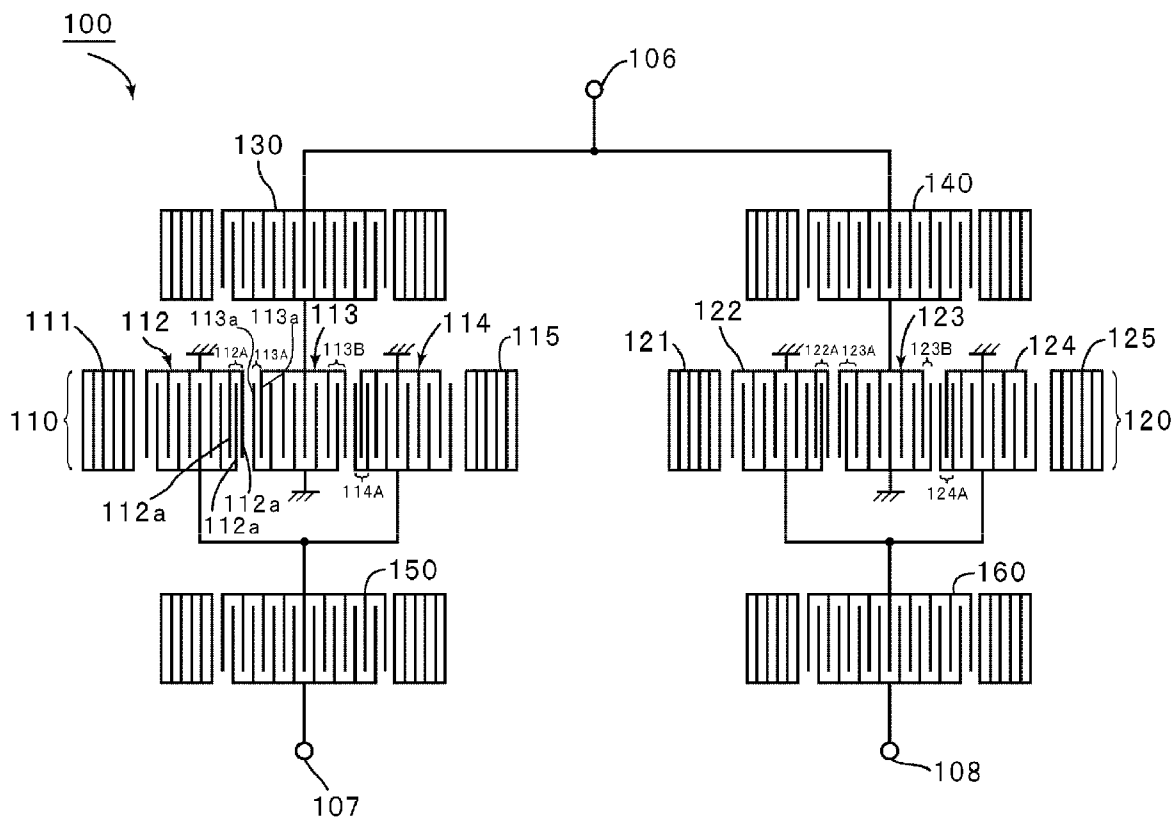


FIG. 1

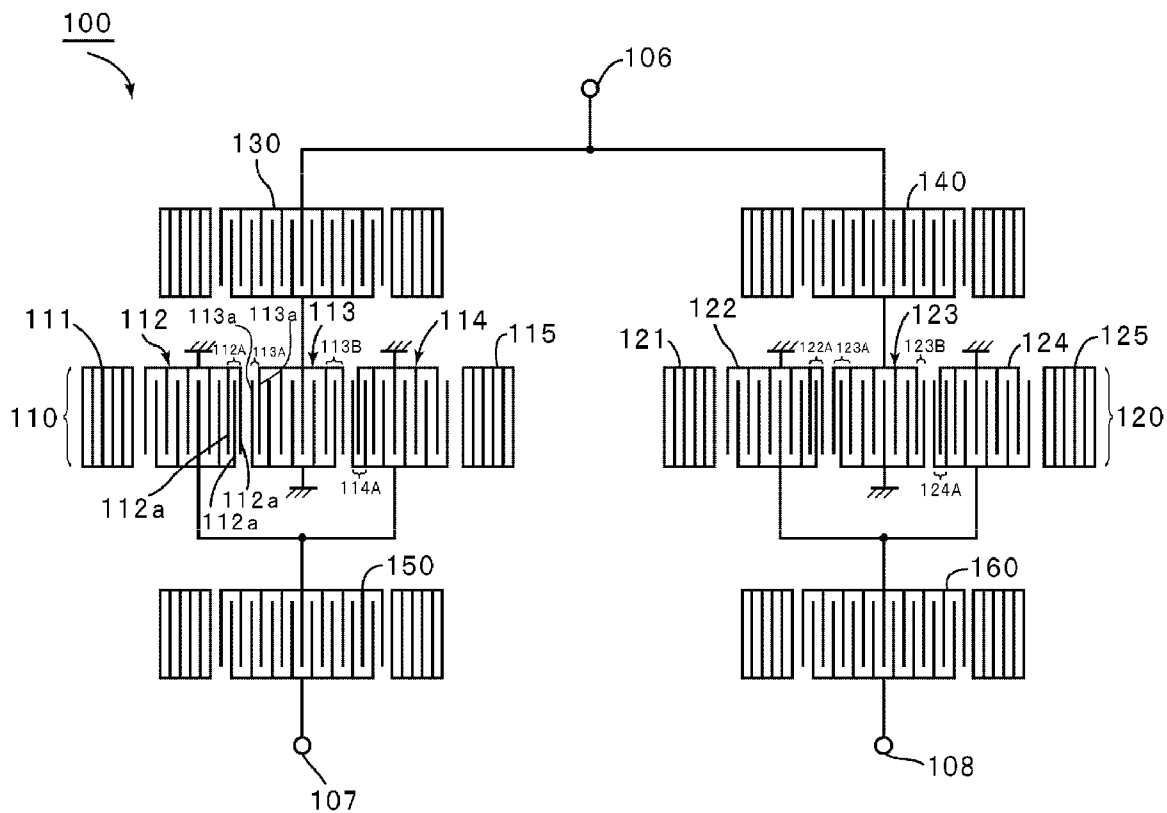


FIG. 2

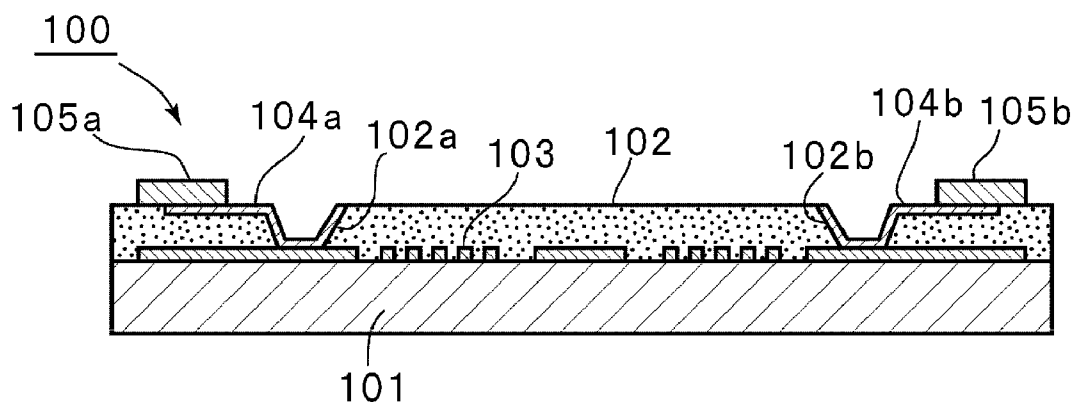


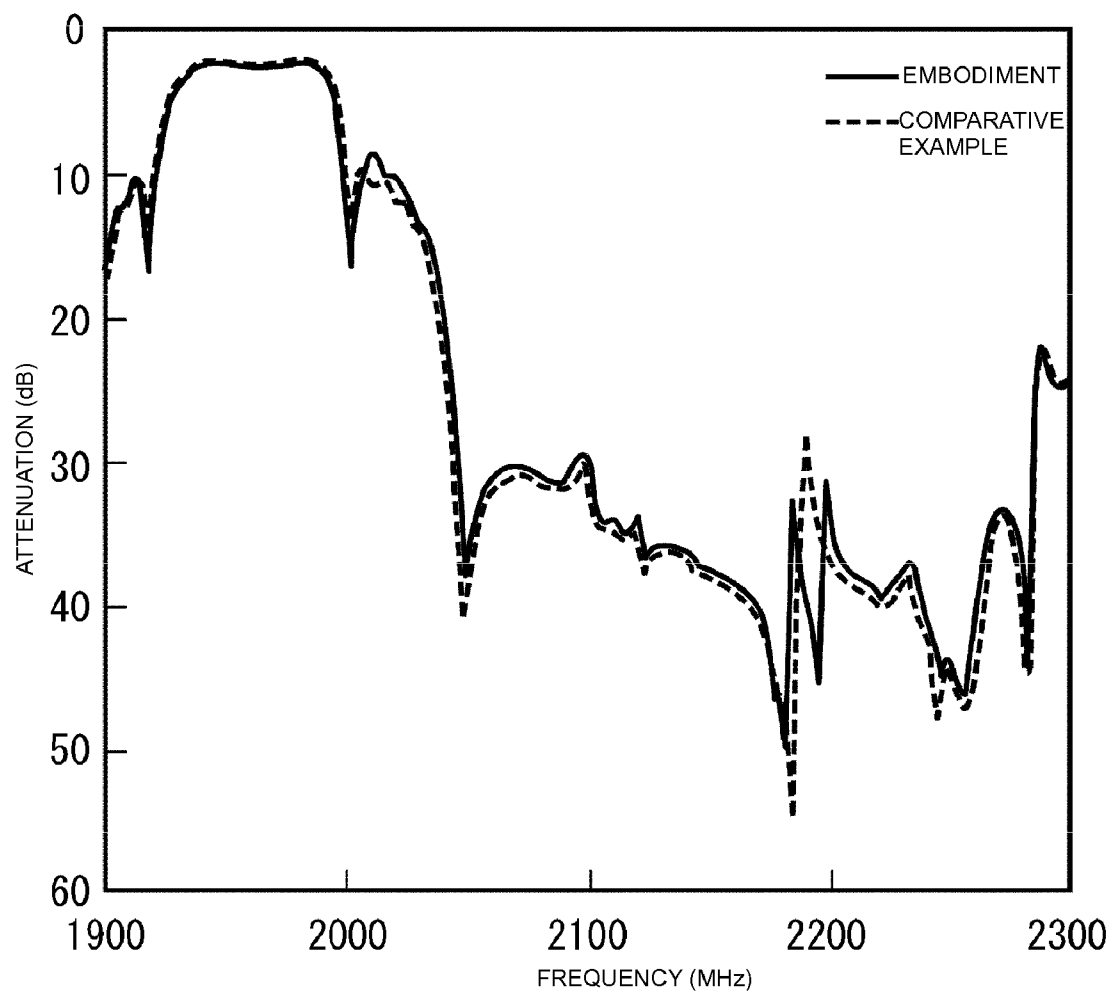
FIG. 3

FIG. 4

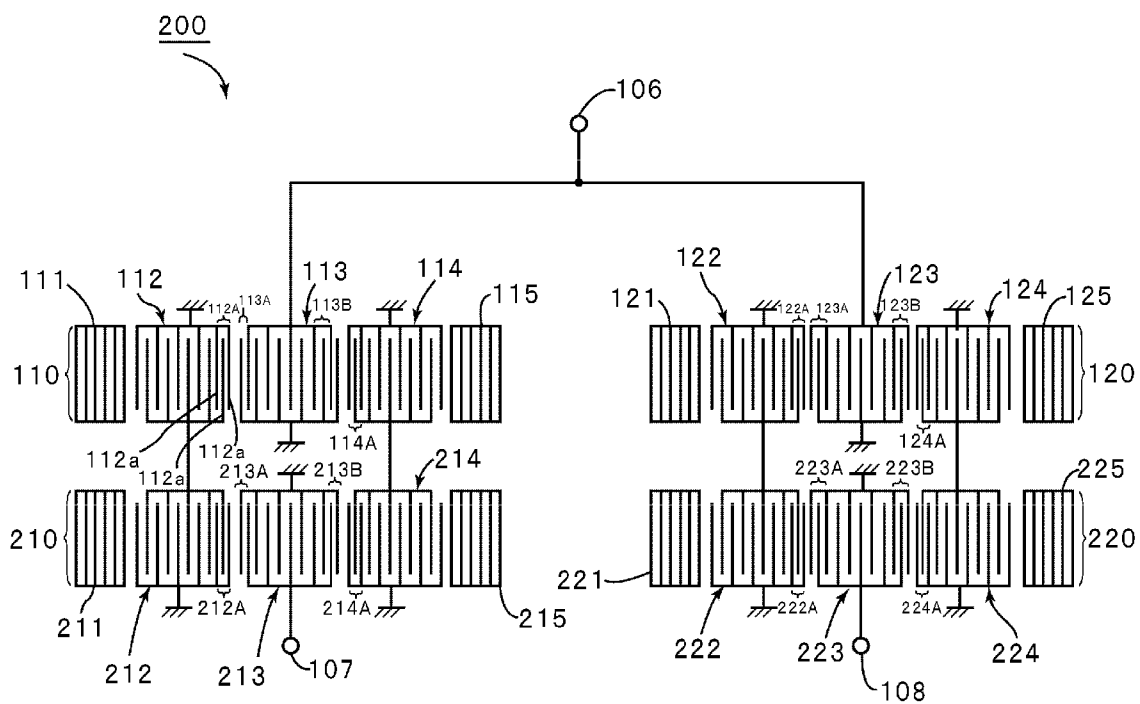


FIG. 5

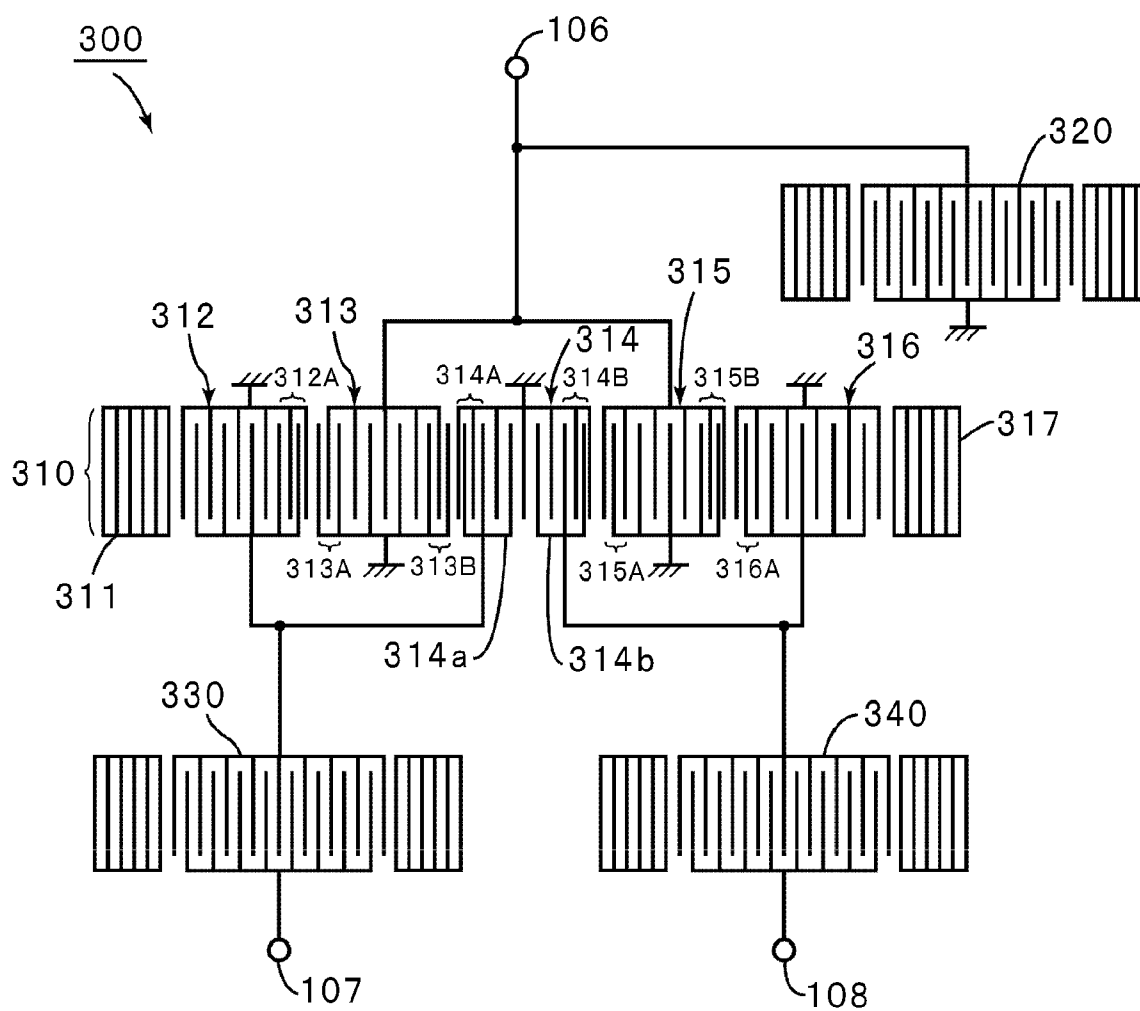


FIG. 6

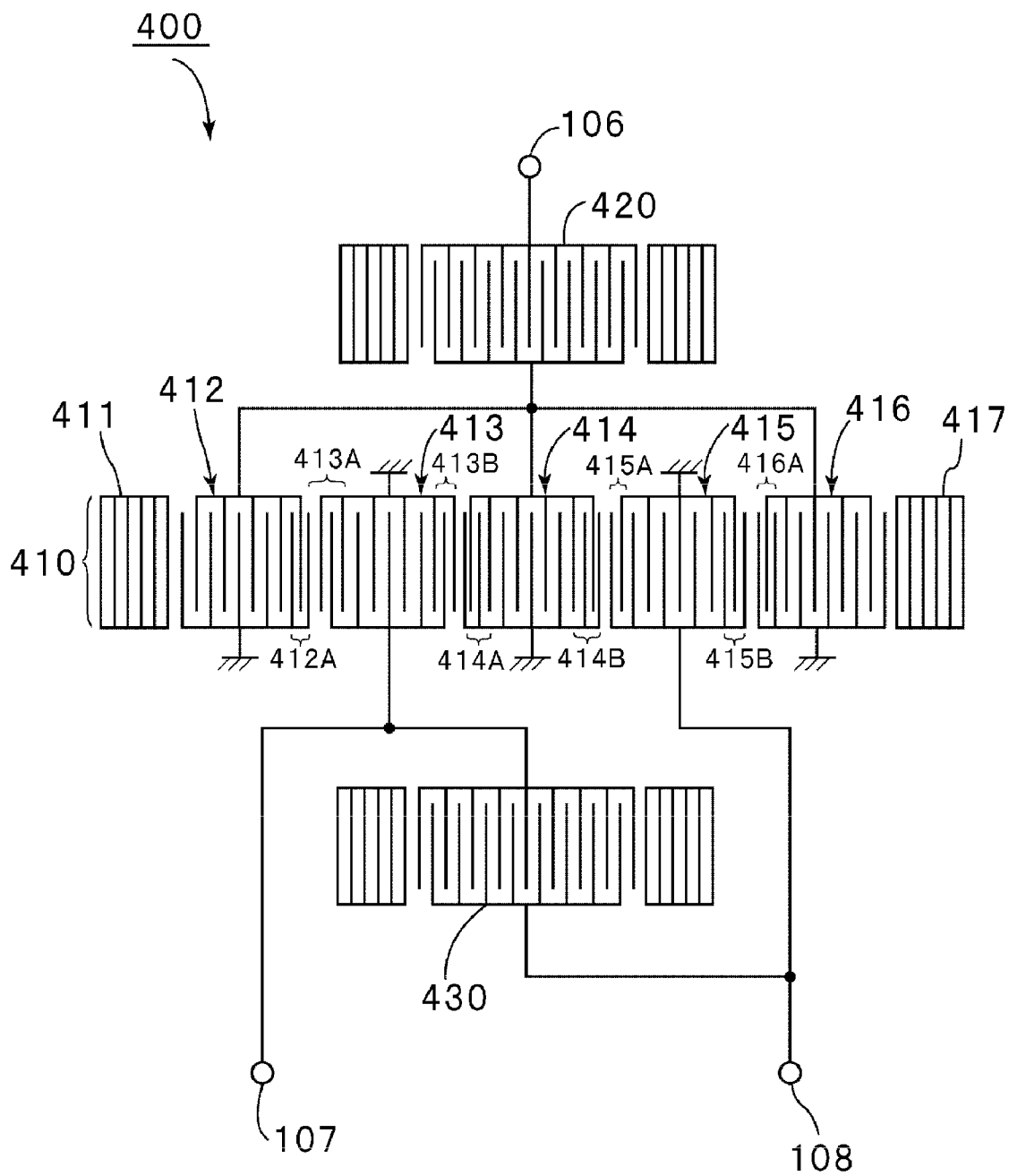
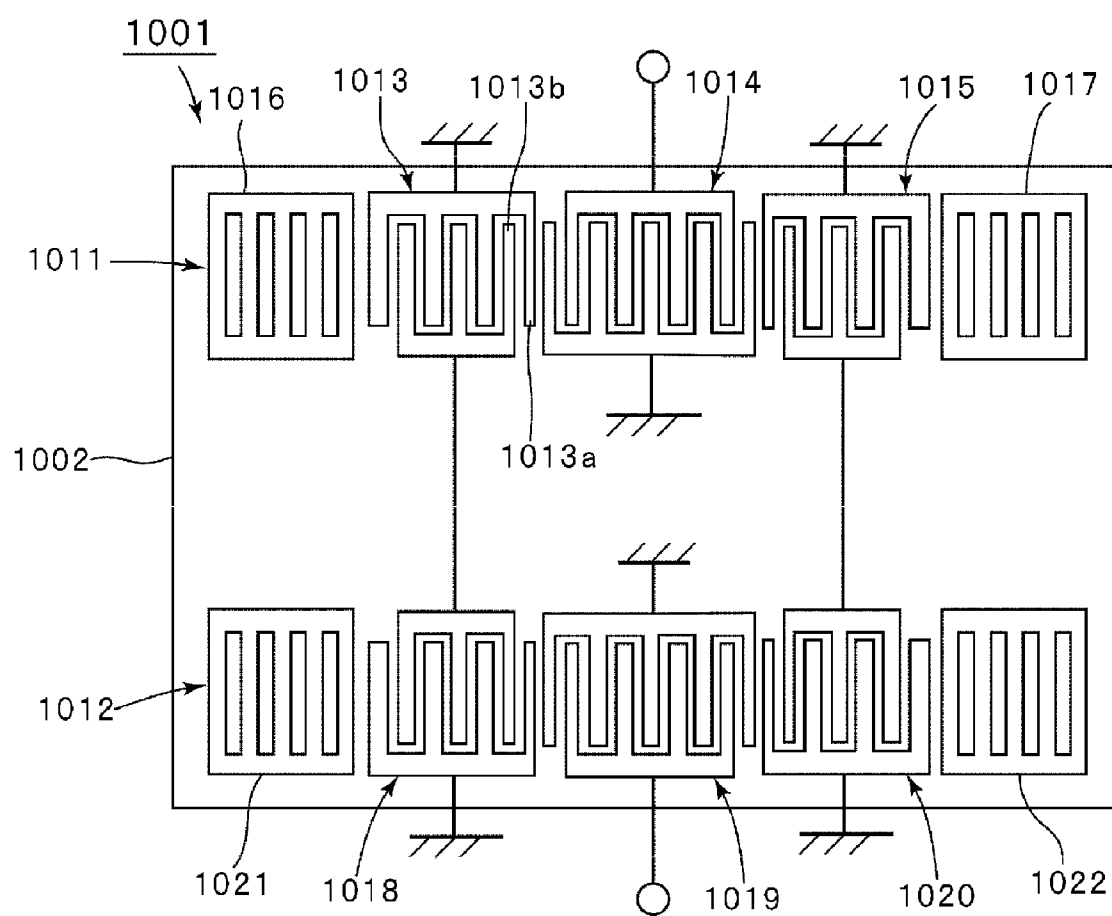


FIG. 7 PRIOR ART



BOUNDARY ACOUSTIC WAVE FILTER

BACKGROUND OF THE INVENTION

[0001] 1. Field of the Invention

[0002] The present invention relates to a boundary acoustic wave filter device used as, for example, a band-pass filter of a cellular phone, and, more particularly, to a longitudinally coupled resonator boundary acoustic wave filter device including a plurality of IDTs that are arranged in a boundary acoustic wave propagating direction.

[0003] 2. Description of the Related Art

[0004] Surface acoustic wave filter devices are widely used as band-pass filters of cellular phones. For example, Japanese Unexamined Patent Application Publication No. 2006-87145 describes a surface acoustic wave filter device having an electrode structure shown in FIG. 7.

[0005] A surface acoustic wave filter device **1001** shown in FIG. 7 includes a piezoelectric substrate **1002**. The electrode structure shown in FIG. 7 is arranged on the piezoelectric substrate **1002** so as to define first and second longitudinally coupled resonator surface acoustic wave filter portions **1011** and **1012**. In the longitudinally coupled resonator surface acoustic wave filter portion **1011**, a first IDT **1014** is arranged in the middle and second and third IDTs **1013** and **1015** are arranged on both sides of the first IDT **1014** in a direction in which a surface acoustic wave propagates. Reflectors **1016** and **1017** are arranged on both sides of the region in which the IDTs **1013** to **1015** are arranged in the direction in which surface acoustic wave propagates.

[0006] Similarly, in the second longitudinally coupled resonator surface acoustic wave filter portion **1012**, a first IDT **1019** is arranged in the middle and second and third IDTs **1018** and **1020** are arranged on both sides of the first IDT **1019** in a direction in which a surface acoustic wave propagates. Reflectors **1021** and **1022** are arranged on both sides of the region in which the IDTs **1018** to **1020** are provided. An input terminal is connected to one end of the first IDT **1014** of the first longitudinally coupled resonator surface acoustic wave filter portion **1011**. An end of the IDTs **1013** and **1015** are respectively connected to an end of the second and third IDTs **1018** and **1020** of the second longitudinally coupled resonator surface acoustic wave filter portion **1012** through signal lines. One end of the middle first IDT **1019** of the second longitudinally coupled resonator surface acoustic wave filter portion **1012** is connected to an output terminal. Ends opposite to the ends of the IDTs **1013** to **1015** and IDTs **1018** to **1020**, to which the input terminal, output terminal and signal lines are connected, are all connected to a ground.

[0007] In the IDTs **1013** to **1015** and IDTs **1018** to **1020** of the surface acoustic wave filter device **1001**, a narrow pitch electrode finger portion is provided in each IDT at a portion at which two IDTs are located adjacent to each other in the direction in which a surface acoustic wave propagates. For example, in the IDT **1013**, a portion of the IDT **1013** including an electrode finger **1013a** located at an end adjacent to the IDT **1014** and an electrode finger **1013b** located next to the electrode finger **1013a** has a relatively narrow pitch. In this manner, the narrow pitch electrode finger portion is provided. The electrode finger pitch of the narrow pitch electrode finger portion is less than the electrode finger pitch of the electrode finger portion of the IDT **1013** other than the narrow pitch electrode finger portion.

[0008] In the longitudinally coupled resonator surface acoustic wave filter device **1001**, because the narrow pitch

electrode finger portion is provided in each IDT at the portion at which two IDTs are located adjacent to each other, an insertion loss can be reduced in a pass band.

[0009] Recently, a boundary acoustic wave filter device that utilizes a boundary acoustic wave that propagates along a boundary between two media having different acoustic velocities has been used. An electrode structure of the boundary acoustic wave device may appropriately utilize the electrode structure of the surface acoustic wave filter device.

[0010] When the boundary acoustic wave filter device includes an electrode structure that is similar to that of the longitudinally coupled resonator surface acoustic wave filter device described in Japanese Unexamined Patent Application Publication No. 2006-87145, an insertion loss in a pass band may be reduced by providing the narrow pitch electrode finger portions. However, a large spurious response tends to occur in a frequency band that is higher than the pass band. Thus, the boundary acoustic wave filter device cannot be used for applications in which the occurrence of a spurious response in a band higher than the pass band is unfavorable.

SUMMARY OF THE INVENTION

[0011] To overcome the problems described above, preferred embodiments of the present invention provide a longitudinally coupled resonator boundary acoustic wave filter device that not only reduces an insertion loss in a pass band by providing a narrow pitch electrode finger portion but also effectively reduces an undesirable spurious response in a frequency band that is higher than the pass band.

[0012] According to a first preferred embodiment of the present invention, a boundary acoustic wave filter device includes a piezoelectric body, a dielectric body laminated on the piezoelectric body, and an electrode structure arranged at a boundary between the piezoelectric body and the dielectric body, wherein the boundary acoustic wave filter device utilizes an SH-type boundary acoustic wave that propagates along the boundary. The electrode structure includes a first IDT, and second and third IDTs that are arranged on both sides of the first IDT in a direction in which the boundary acoustic wave propagates, whereby a longitudinally coupled resonator boundary acoustic wave filter portion is provided, wherein in the first to third IDTs, in a region in which two IDTs are located adjacent to each other, the electrode finger pitch of a portion of electrode fingers of one IDT, located at an end adjacent to the other IDT, is less than the electrode finger pitch of a portion of electrode fingers of the one IDT, adjacent to that portion, whereby a narrow pitch electrode finger portion is provided, and wherein the electrode finger pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions provided in the first IDT and the second and third IDTs is different from the electrode finger pitch of the electrode finger portions of each of the remaining narrow pitch electrode finger portions.

[0013] According to a second preferred embodiment of the present invention, a boundary acoustic wave filter device includes a piezoelectric body, a dielectric body laminated on the piezoelectric body, and an electrode structure arranged at a boundary between the piezoelectric body and the dielectric body. The boundary acoustic wave filter device utilizes an SH-type boundary acoustic wave that propagates along the boundary, wherein the electrode structure includes first and second longitudinally coupled resonator filter portions, each of which includes a first IDT, and second and third IDTs that are arranged on both sides of the first IDT in a direction in

which the boundary acoustic wave propagates, wherein at portions of the first to third IDTs, at which two IDTs are located adjacent to each other, the pitch of a portion of electrode fingers of one IDT, located at an end adjacent to the other IDT, is less than the pitch of another portion of electrode fingers of the one IDT, adjacent to that portion, whereby a narrow pitch electrode finger portion is provided, wherein the polarity of each of the first to third IDTs of the first and second longitudinally coupled resonator boundary acoustic wave filter portions is selected such that the phase of an output signal to an input signal of the second longitudinally coupled resonator boundary acoustic wave filter portion is different by about 180 degrees from the phase of an output signal to an input signal of the first longitudinally coupled resonator boundary acoustic wave filter portion, wherein an unbalanced terminal and first and second balanced terminals are provided, input ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are connected to the unbalanced terminal, and output ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are respectively connected to the first and second balanced terminals, and wherein the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions of the first IDT and the second and third IDTs is different from the pitch of the electrode finger portions of each of the remaining narrow pitch electrode finger portions.

[0014] According to a third preferred embodiment of the present invention, a boundary acoustic wave filter device includes a piezoelectric body, a dielectric body laminated on the piezoelectric body, and an electrode structure arranged at a boundary between the piezoelectric body and the dielectric body, wherein the boundary acoustic wave filter device utilizes an SH-type boundary acoustic wave that propagates along the boundary. The electrode structure includes first and second longitudinally coupled resonator filter portions, each of which includes a first IDT, and second and third IDTs that are arranged on both sides of the first IDT in a direction in which the boundary acoustic wave propagates, wherein at portions of the first to third IDTs, at which two IDTs are located adjacent to each other, the pitch of a portion of electrode fingers of one IDT, located at an end adjacent to the other IDT, is less than the pitch of another portion of electrode fingers of the one IDT, adjacent to that portion, whereby a narrow pitch electrode finger portion is provided, wherein the polarity of each of the first to third IDTs of the first and second longitudinally coupled resonator boundary acoustic wave filter portions is selected such that the phase of an output signal to an input signal of the second longitudinally coupled resonator boundary acoustic wave filter portion is different by about 180 degrees from the phase of an output signal to an input signal of the first longitudinally coupled resonator boundary acoustic wave filter portion, wherein an unbalanced terminal and first and second balanced terminals are provided, input ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are connected to the unbalanced terminal, and output ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are connected to the first and second balanced terminals, wherein the pitches of the electrode fingers of the narrow pitch electrode finger portions of the first to third IDTs in the first longitudinally coupled resonator filter portion are equal or substantially equal to one another, wherein the pitches of the electrode fingers of the

narrow pitch electrode finger portions of the first to third IDTs in the second longitudinally coupled resonator filter portion are equal or substantially equal to one another, and wherein the pitch of the electrode fingers of each of the narrow pitch electrode finger portions of the first to third IDTs in the first longitudinally coupled resonator filter portion is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions of the first to third IDTs in the second longitudinally coupled resonator filter portion.

[0015] In the boundary acoustic wave filter device according to the second or third preferred embodiment, the boundary acoustic wave filter device preferably further includes third and fifth longitudinally coupled resonator boundary acoustic wave filter portions that are configured the same or substantially the same as the first longitudinally coupled resonator boundary acoustic wave filter portion, and fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions that are configured the same or substantially the same as the second longitudinally coupled resonator boundary acoustic wave filter portion, wherein input ends of the first to sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the unbalanced terminal, output ends of the first, third and fifth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the first balanced terminal, and output ends of the second, fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the second balanced terminal. In this case, because the third and fifth longitudinally coupled resonator boundary acoustic wave filter portions are connected in parallel with the first longitudinally coupled resonator boundary acoustic wave filter portion, and the fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected in parallel with the second longitudinally coupled resonator boundary acoustic wave filter portion, a boundary acoustic wave filter device is provided which has enhanced power withstanding capability with less loss.

[0016] In the boundary acoustic wave filter device according to the first or second preferred embodiment, preferably, the number of electrode fingers of each of the narrow pitch electrode finger portions of the first IDT is different from the number of electrode fingers of each of the narrow pitch electrode finger portions of the second and third IDTs. In this case, by adjusting the number of electrode fingers of each IDT, unwanted spurious responses are effectively prevented.

[0017] The boundary acoustic wave filter device according to a preferred embodiment of the present invention may preferably further include fourth and fifth IDTs, the fourth and fifth IDTs being arranged on both sides of the region in which the first to third IDTs are provided, in the direction in which the boundary acoustic wave propagates, whereby a five-IDT type longitudinally coupled resonator boundary acoustic wave filter portion is provided. Thus, a boundary acoustic wave filter device is provided which has further enhanced power withstanding capability with less loss.

[0018] In the boundary acoustic wave filter device according to the first preferred embodiment, because the narrow pitch electrode finger portions are provided in the first to third IDTs, an insertion loss within the pass band is reduced. In addition, because, the pitch of at least one of the narrow pitch electrode finger portions is different from the pitch of the electrode fingers of each of the remaining narrow pitch electrode finger portions, the influence of the at least one of the narrow pitch electrode finger portions on the filter character-

istic is different from the influence of the remaining narrow pitch electrode finger portions on the filter characteristic. Thus, an undesirable spurious response that occurs in a band higher than the pass band is reduced.

[0019] Similarly, according to the second preferred embodiment, because each of the first and second longitudinally coupled resonator boundary acoustic wave filter portions has first to third IDTs, an insertion loss in the pass band is reduced. In addition, the pitch of at least one of the narrow pitch electrode finger portions is different from the pitch of the electrode fingers of each of the remaining narrow pitch electrode finger portions. Thus, an undesirable spurious response that occurs in a band higher than the pass band is reduced.

[0020] In the first and second preferred embodiments, the reason that a high band side spurious response is suppressed in such a manner that the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions of the first to third IDTs is different from the pitch of the remaining narrow pitch electrode finger portions may be as follows. In the boundary acoustic wave filter device that utilizes an SH-type boundary acoustic wave, a cut angle of the piezoelectric body and a normalized thickness of an IDT ($\text{IDT thickness / IDT wavelength}$) are usually set in a range in which the electromechanical coefficient for a Stoneley wave that causes a spurious response is small. On the other hand, the thickness of each IDT is the same or substantially the same. Thus, even when the narrow pitch electrode finger portions are provided, the thickness of each narrow pitch electrode finger portion is usually the same or substantially the same as the remaining portions of the IDTs. As a result, the normalized thickness of the narrow pitch electrode finger portion shifts from a range in which the electromechanical coefficient for a Stoneley wave is relatively small in a direction in which the normalized thickness increases. Thus, in the narrow pitch electrode finger portion, the excited Stoneley wave is received at a particular strength, such that the above described spurious response occurs in a frequency band higher than the pass band.

[0021] In contrast, in the first and second preferred embodiments of the present invention, because the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions is different from the pitch of the electrode fingers of each of the remaining narrow pitch electrode finger portions, the frequency band of an excited Stoneley wave received by the at least one of the narrow pitch electrode finger portions is shifted from a frequency band of an excited Stoneley wave received by the remaining narrow pitch electrode finger portions. Thus, a spurious response that occurs in a band higher than the pass band is dispersed and thus, the spurious response is reduced.

[0022] Therefore, according to the first and second preferred embodiments of the present invention, it is possible to suppress a spurious response in a frequency band higher than the pass band. Thus, it is possible to provide a boundary acoustic wave filter device that is suitable for applications in which the occurrence of a large spurious response in a band higher than the pass band is unfavorable.

[0023] In the boundary acoustic wave filter device according to the third preferred embodiment of the present invention, in a configuration in which the balance-unbalance conversion function is provided and the first and second longitudinally coupled resonator filter portions are connected to the first and second balanced terminals, the pitch of the electrode fingers of each of the narrow pitch electrode finger

portions of the first to third IDTs in the first longitudinally coupled resonator filter portion is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions of the first to third IDTs in the second longitudinally coupled resonator filter portion. Thus, it is possible to reduce an undesirable spurious response that appears in a band higher than the pass band. That is, the influence of the narrow pitch electrode finger portions of the first longitudinally coupled resonator filter portion on the filter characteristic is different from the influence of the narrow pitch electrode finger portions of the second longitudinally coupled resonator filter portion on the filter characteristic, such that it is possible to disperse a spurious response in a high band side so as to reduce the high-band side spurious response.

[0024] Other features, elements, steps, characteristics and advantages of the present invention will become more apparent from the following detailed description of preferred embodiments of the present invention with reference to the attached drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0025] FIG. 1 is a schematic plan view that shows the electrode structure of a boundary acoustic wave filter device according to a first preferred embodiment of the present invention.

[0026] FIG. 2 is a schematic front cross-sectional view of the boundary acoustic wave filter device according to the first preferred embodiment of the present invention.

[0027] FIG. 3 is a view that shows the filter characteristic of the boundary acoustic wave filter device according to the first preferred embodiment of the present invention and the filter characteristic of a boundary acoustic wave filter device according to a prepared comparative example.

[0028] FIG. 4 is a schematic plan view that shows the electrode structure of a boundary acoustic wave filter device according to a second preferred embodiment of the present invention.

[0029] FIG. 5 is a schematic plan view that shows the electrode structure of a boundary acoustic wave filter device according to a third preferred embodiment of the present invention.

[0030] FIG. 6 is a schematic plan view that shows the electrode structure of a boundary acoustic wave filter device according to an alternative example of a preferred embodiment of the present invention.

[0031] FIG. 7 is a schematic plan view that shows the electrode structure of a known longitudinally coupled resonator surface acoustic wave filter device.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

[0032] Hereinafter, specific preferred embodiments of the present invention will be described with reference to the accompanying drawings.

[0033] FIG. 1 is a schematic plan view that shows the electrode structure of a longitudinally coupled resonator boundary acoustic wave filter device according to a first preferred embodiment of the present invention. FIG. 2 is a schematic front cross-sectional view of the boundary acoustic wave filter device.

[0034] As shown in FIG. 2, the boundary acoustic wave filter device 100 includes a piezoelectric substrate 101 made of LiNbO_3 having a principal plane obtained by rotating the

Y-axis through about 15 degrees \pm 10 degrees. A dielectric body **102** is laminated on the piezoelectric substrate **101**. In the present preferred embodiment, the dielectric body **102** is preferably made of silicon oxide, for example. The silicon oxide may preferably include SiO₂, for example. However, the dielectric body **102** may preferably be made of another dielectric body material other than silicon oxide, such as silicon nitride, for example.

[0035] An electrode structure **103** is provided at a boundary between the piezoelectric substrate **101** and the dielectric body **102**. The electrode structure **103** is schematically shown in FIG. 1.

[0036] As shown in FIG. 2, the dielectric body **102** is provided with a plurality of openings **102a** and **102b**. A portion of the electrode structure **103** is exposed at the openings **102a** and **102b**. Then, conductive patterns **104a** and **104b** are provided at the openings **102a** and **102b**. The conductive patterns **104a** and **104b** are electrically connected to the electrode structure that is exposed in the opening, and extend onto the upper surface of the dielectric body **102** outside the openings. Then, the conductive patterns **104a** and **104b** are electrically connected to the external electrodes **105a** and **105b**, respectively. The external electrodes **105a** and **105b** correspond to terminals that are connected to an unbalanced terminal, a balanced terminal, which will be described later, or a ground.

[0037] The boundary acoustic wave filter device **100** is preferably a longitudinally coupled resonator boundary acoustic wave filter device that utilizes an SH-type boundary acoustic wave, which propagates along a boundary between the piezoelectric substrate **101** and the dielectric body **102**.

[0038] The boundary acoustic wave filter device **100** is preferably used as a GSM 1900 MHz band receiving filter having a pass band of about 1930 MHz to about 1990 MHz, for example.

[0039] As shown in FIG. 1, the boundary acoustic wave filter device **100** includes the illustrated electrode structure between an unbalanced terminal **106** and first and second balanced terminals **107** and **108**.

[0040] A first longitudinally coupled resonator boundary acoustic wave filter portion **110** is connected to the unbalanced terminal **106** via a one-port boundary acoustic wave resonator **130**. In addition, the first longitudinally coupled resonator boundary acoustic wave filter portion **110** is connected to the first balanced terminal **107** via a one-port boundary acoustic wave resonator **150**.

[0041] Each of the one-port boundary acoustic wave resonators **130** and **150** includes an IDT and reflectors arranged on both sides of the IDT in a boundary acoustic wave propagating direction in which a boundary acoustic wave propagates.

[0042] On the other hand, the first longitudinally coupled resonator boundary acoustic wave filter portion **110** includes a first IDT **113**, second and third IDTs **112** and **114**, and reflectors **111** and **115**. The first IDT **113** is arranged in the middle. The second and third IDTs **112** and **114** are arranged on both sides of the first IDT **113** in the boundary acoustic wave propagating direction. The reflectors **111** and **115** are arranged on both sides of the region in which the first to third IDTs **113**, **112**, and **114** are arranged in the boundary acoustic wave propagating direction.

[0043] The longitudinally coupled resonator boundary acoustic wave filter portion **110** is preferably the three-IDT type longitudinally coupled resonator filter described above. At a portion at which the first and second IDTs **112** and **113** are located adjacent to each other and at a portion at which the

first and third IDTs **113** and **114** are located adjacent to each other, each of the IDTs **112** to **114** includes a narrow pitch electrode finger portion.

[0044] That is, the electrode finger pitch of a portion of an end of the second IDT **112** adjacent to the first IDT **113** at which a plurality of electrode fingers **112a** are provided defines a narrow pitch electrode finger portion **112A** having a reduced pitch of the electrode fingers. The electrode finger pitch of the electrode fingers of the narrow pitch electrode finger portion **112A** is less than the electrode finger pitch of the remaining portion of the IDT **112**, adjacent to the narrow pitch electrode finger portion **112A**.

[0045] On the other hand, a narrow pitch electrode finger portion **113A** is provided at an end of the first IDT **113**, adjacent to the second IDT **112**. The narrow pitch electrode finger portion **113A** includes a plurality of electrode fingers **113a**. The electrode finger pitch of the electrode fingers of the narrow pitch electrode finger portion **113A** is less than the electrode finger pitch of the IDT **113**, adjacent to the narrow pitch electrode finger portion **113A**. Note that a narrow pitch electrode finger portion **113B** is also provided in the first IDT **113** adjacent to the third IDT **114**.

[0046] In the first longitudinally coupled resonator boundary acoustic wave filter portion, the narrow pitch electrode finger portions **112A**, **113A**, **113B** and **114A** are provided in the IDTs **112** to **114**.

[0047] In the present preferred embodiment, the electrode finger pitch of each of the narrow pitch electrode finger portions **112A**, **113A**, **113B** and **114A** of the first longitudinally coupled resonator boundary acoustic wave filter portion **110** is less than the electrode finger pitch of each of narrow pitch electrode finger portions **122A**, **123A**, **123B** and **124A** of a second longitudinally coupled resonator boundary acoustic wave filter portion **120**.

[0048] As shown in FIG. 1, the second longitudinally coupled resonator boundary acoustic wave filter portion **120** is connected to the unbalanced terminal **106** via a one-port boundary acoustic wave resonator **140**. In addition, the second longitudinally coupled resonator boundary acoustic wave filter portion **120** is connected to the second balanced terminal **108** via a one-port boundary acoustic wave resonator **160**.

[0049] The one-port boundary acoustic wave resonators **140** and **160** are similar to the one-port boundary acoustic wave resonators **130** and **150**.

[0050] The second longitudinally coupled resonator boundary acoustic wave filter portion **120** includes a first IDT **123**, second and third IDTs **122** and **124**, and reflectors **121** and **125**. The first IDT **123** is arranged in the middle. The second and third IDTs **122** and **124** are arranged on both sides of the first IDT **123** in boundary acoustic wave propagating direction.

[0051] The second longitudinally coupled resonator boundary acoustic wave filter portion **120** is similar to the first longitudinally coupled resonator boundary acoustic wave filter portion **110**, except that the polarity of the middle first IDT **123** is opposite to the polarity of the first IDT **113**. That is, in the second longitudinally coupled resonator boundary acoustic wave filter portion **120**, at a portion at which the first and second IDTs **123** and **122** are located adjacent to each other and at a portion at which the first and third IDTs **123** and **124** are located adjacent to each other, narrow pitch electrode finger portions **122A**, **123A**, **123B**, and **124A** are provided in the IDTs **122** to **124**.

[0052] In the longitudinally coupled resonator boundary acoustic wave filter portion 120, the pitch of the electrode fingers of each of the narrow pitch electrode finger portions 122A and 124A of the first and third IDTs is less than the pitch of the electrode fingers of each of the narrow pitch electrode finger portions 123A and 123B of the first IDT 123.

[0053] Note that in the boundary acoustic wave filter device 100, the boundary acoustic wave propagating direction in each of the first and second longitudinally coupled resonator boundary acoustic wave filter portions is preferably $\psi=20^\circ$, for example, the boundary acoustic wave propagating direction in each of the one-port boundary acoustic wave resonators 130 and 140 is preferably $\psi=10^\circ$, for example, and the boundary acoustic wave propagating direction in each of the one-port boundary acoustic wave resonators 150 and 160 is preferably $\psi=30^\circ$, for example. That is, by differentiating the propagating directions of the boundary acoustic waves, it is possible to set an electromechanical coefficient to an appropriate value.

[0054] However, in preferred embodiments of the present invention, it is not always necessary to vary the boundary acoustic wave propagating direction of each of the longitudinally coupled resonator boundary acoustic wave filter portions from the boundary acoustic wave propagating direction of each of the boundary acoustic wave resonators. In addition, it is not always necessary to provide the boundary acoustic wave resonators 130, 140, 150, and 160.

[0055] In the longitudinally coupled resonator boundary acoustic wave filter device 100, because the above electrode structure is provided between the unbalanced terminal 106 and the first and second balanced terminals 107 and 108, a band-pass filter having a balance-unbalance conversion function is provided. In the first and second longitudinally coupled resonator boundary acoustic wave filter portions 110 and 120, because the narrow pitch electrode finger portions 112A, 113A, 113B, 114A, 122A, 123A, 123B and 124A are provided, continuity of a portion at which IDTs are located adjacent to each other is enhanced. Thus, an insertion loss in the pass band can be reduced.

[0056] This is advantageous because the narrow pitch electrode finger portions are provided as in the case of the surface acoustic wave filter device described in Japanese Unexamined Patent Application Publication No. 2006-87145.

[0057] As mentioned above, in the present preferred embodiment, the electrode finger pitch of each of the narrow pitch electrode finger portions 112A, 113A, 113B and 114A of the first longitudinally coupled resonator boundary acoustic wave filter portion 110 is less than the pitch of the electrode fingers of each of the narrow pitch electrode finger portions 122A, 123A, 123B and 124A of the second longitudinally coupled resonator boundary acoustic wave filter portion 120. With this configuration, an unnecessary spurious response in a frequency band that is higher than the pass band is effectively reduced. This will be described with reference to FIG. 3.

[0058] FIG. 3 shows the filter characteristics of the longitudinally coupled resonator boundary acoustic wave filter device according to the present preferred embodiment and the filter characteristics of a boundary acoustic wave filter device according to a comparative example. In the boundary acoustic wave filter device of the present preferred embodiment, the electrode finger pitch λ of the electrode fingers of each IDT other than the narrow pitch electrode finger portions is preferably set to about $1.675\ \mu\text{m}$, the electrode finger pitch of the

electrode fingers of each of the narrow pitch electrode finger portions 112A, 113A, 113B and 114A of the first longitudinally coupled resonator boundary acoustic wave filter portion 110 is preferably set to about $1.46634\ \mu\text{m}$, and the electrode finger pitch of the electrode fingers of each of the narrow pitch electrode finger portions 122A, 123A, 123B and 124A of the second longitudinally coupled resonator boundary acoustic wave filter portion 120 is preferably set to about $1.48634\ \mu\text{m}$, for example.

[0059] On the other hand, in the boundary acoustic wave filter device according to the comparative example, the electrode finger pitch of each of the narrow pitch electrode finger portions is set to about $1.47634\ \mu\text{m}$, and the electrode finger pitch of the electrode fingers of each of the remaining main electrode portions is set to about $1.675\ \mu\text{m}$. Other than this difference, the boundary acoustic wave filter device according to the comparative example is manufactured in a similar manner to the present preferred embodiment. Note that in each of the preferred embodiment and the comparative example, the narrow pitch electrode finger portions 112A, 113A, 113B, 114A, 122A, 123A, 123B, and 124A include three electrode fingers. In FIG. 3, the solid line represents the result of the present preferred embodiment, and the broken line represents the result of the comparative example.

[0060] As shown in FIG. 3, around 2190 MHz, which is higher in than about 1930 MHz to about 1990 MHz, which is the PCS receiving band and is the pass band, a large spurious response occurred. In contrast, in the boundary acoustic wave filter device of the present preferred embodiment, it appears that a spurious response around 2190 MHz is significantly reduced and the spurious response is improved by about 3 dB. In addition, it appears that the attenuation around 2190 MHz is improved from about 28.4 dB to about 31.5 dB according to the present preferred embodiment.

[0061] As described above, the reason that a spurious response around 2190 MHz is improved may be as follows.

[0062] The spurious response is an unwanted mode caused by a Stoneley wave that causes a spurious response against an SH-type boundary acoustic wave. Then, when designing a boundary acoustic wave filter device that utilizes an SH wave, the thickness of an IDT is usually set to a thickness having a relatively small electromechanical coefficient for the Stoneley wave. When the thickness of the IDT is considered, a range in which the electromechanical coefficient for the Stoneley wave is relatively small is set using a numeric value represented by a normalized thickness ($=(\text{electrode thickness}/\text{electrode interval})$). However, because the normalized thickness depends on the pitch of the electrode fingers, at the narrow pitch electrode finger portions, excited Stoneley waves are received at a specific strength. Thus, the above described spurious response occurs.

[0063] In contrast, in the present preferred embodiment, the pitch of the electrode fingers of each of the narrow pitch electrode finger portions 112A, 113A, 113B and 114A of the first longitudinally coupled resonator boundary acoustic wave filter portion 110 is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions 122A, 123A, 123B and 124A of the second longitudinally coupled resonator boundary acoustic wave filter portion 120. Thus, the spurious responses occur at shifted positions and, therefore, the size of the spurious is reduced.

[0064] Thus, according to the present preferred embodiment, it is possible to provide a filter device that is suitable for applications that require that an undesirable spurious

response does not occur in a band higher than the pass band, for example, in a transmitting side pass band, such as a PCS receiving band-pass filter.

[0065] Note that in the present preferred embodiment, the pitch of the electrode fingers of each narrow pitch electrode finger portion of the first longitudinally coupled resonator boundary acoustic wave filter portion **110** is preferably set to be less than the pitch of the electrode fingers of each narrow pitch electrode finger portion of the second longitudinally coupled resonator boundary acoustic wave filter portion. However, the pitch may be set to be greater than the pitch of the electrode fingers of each narrow pitch electrode finger portion of the second longitudinally coupled resonator boundary acoustic wave filter portion.

[0066] Note that in the first preferred embodiment, the pitch of each narrow pitch electrode finger portion of the first longitudinally coupled resonator boundary acoustic wave filter portion is preferably varied from the pitch of the electrode fingers of each narrow pitch electrode finger portion of the second longitudinally coupled resonator boundary acoustic wave filter portion. However, in the first longitudinally coupled resonator boundary acoustic wave filter portion **110**, the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions may be varied from the pitch of the electrode fingers of each of the remaining narrow pitch electrode finger portions, and in the second longitudinally coupled resonator boundary acoustic wave filter portion, the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions may be varied from the pitch of each of the remaining narrow pitch electrode finger portions.

[0067] That is, as described above, a spurious response that occurs in a filter characteristic is dispersed by the narrow pitch electrode finger portions and the size of the spurious response that occurs in a band higher than the pass band is reduced. Thus, in one longitudinally coupled resonator boundary acoustic wave filter, for example, the pitch of the electrode fingers of each narrow pitch electrode finger portion of the first IDT **113** may preferably be set to be greater or less than the pitch of the electrode fingers of each of the narrow pitch electrode finger portions of the second and third IDTs. Then, in the preferred embodiment in which the first and second longitudinally coupled resonator boundary acoustic wave filter portions are provided, in at least one of the first and second longitudinally coupled resonator boundary acoustic wave filter portions, as described above, the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions is varied from the pitch of the electrode fingers of each of the remaining narrow pitch electrode finger portions. Thus, it is possible to disperse spurious responses that occur in a high band side to reduce the spurious response.

[0068] In addition, according to a modification of the first preferred embodiment, not only the pitches of the electrode fingers of the narrow pitch electrode finger portions can preferably be varied, but also the numbers of electrode fingers can be varied, such that it is possible to disperse and further reduce the spurious response. Thus, in this modification, in which the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions is varied from the pitch of each of the remaining narrow pitch electrode finger portions, preferably, for example, the number of electrode fingers of each narrow pitch electrode finger portion of the first IDT is also varied from the number of electrode fingers of each narrow pitch electrode finger portion of the second and third IDTs.

[0069] However, the number of electrode fingers of each of the narrow pitch electrode finger portions of the first IDT may be equal to the number of electrode fingers of each of the narrow pitch electrode finger portions of the second and third IDTs.

[0070] FIG. **4** is a schematic plan view that shows the electrode structure of a boundary acoustic wave filter device according to a second preferred embodiment of the present invention.

[0071] In the boundary acoustic wave filter device of the first preferred embodiment shown in FIG. **1**, the one-port boundary acoustic wave resonators are connected respectively to the preceding stage and following stage of each of the first and second longitudinally coupled resonator boundary acoustic wave filter portions **110** and **120**. In the boundary acoustic wave filter device **200** shown in FIG. **4**, the first and second longitudinally coupled resonator boundary acoustic wave filter portions **110** and **120** are directly connected to the unbalanced terminal **106**. Then, third and fourth longitudinally coupled resonator boundary acoustic wave filter portions **210** and **220** are respectively connected to the following stages of the first and second longitudinally coupled resonator boundary acoustic wave filter portions **110** and **120**. The longitudinally coupled resonator boundary acoustic wave filter portions **210** and **220** are preferably three-IDT type longitudinally coupled resonator boundary acoustic wave filter portions, similar to the longitudinally coupled resonator boundary acoustic wave filter portions **110** and **120**.

[0072] However, the longitudinally coupled resonator boundary acoustic wave filter portions **210** and **220** are configured in substantially the same manner as the first longitudinally coupled resonator boundary acoustic wave filter portion **110**. That is, IDTs **212** to **214** in the longitudinally coupled resonator boundary acoustic wave filter portion **210**, IDTs **222** to **224** in the longitudinally coupled resonator boundary acoustic wave filter portion **220**, and the IDTs **112** to **114** in the first longitudinally coupled resonator boundary acoustic wave filter portion **110** have the same polarity among the corresponding IDTs.

[0073] Then, ends of the second and third IDTs **112** and **114** of the first longitudinally coupled resonator boundary acoustic wave filter portion **110** are respectively connected to ends of the second and third IDTs **212** and **214** of the third longitudinally coupled resonator boundary acoustic wave filter portion **210**. The other ends of the IDTs **212** and **214** are connected to a ground. One end of the middle first IDT **213** is connected to a ground, and the other end thereof is connected to the first balanced terminal **107**. Similarly, ends of the second and third IDTs **222** and **224** of the fourth longitudinally coupled resonator boundary acoustic wave filter portion **220** are respectively connected to the second and third IDTs **122** and **124** of the second longitudinally coupled resonator boundary acoustic wave filter portion **120**, and the other ends thereof are connected to a ground. One end of the first IDT **223** is connected to a ground, and the other end thereof is connected to the second balanced terminal **108**.

[0074] In the longitudinally coupled resonator boundary acoustic wave filter device **200** of the present preferred embodiment, in the third and fourth longitudinally coupled resonator boundary acoustic wave filter portions **210** and **220**, narrow pitch electrode finger portions **212A**, **213A**, **213B**, **214A**, **222A**, **223A**, **223B**, and **224A** are provided at portions at which IDTs are located adjacent to each other. Then, the pitch of the electrode fingers of each of the narrow pitch

electrode finger portions **213A**, **213B**, **212A** and **214A** is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions **223A**, **223B**, **222A** and **224A**.

[0075] In the boundary acoustic wave filter device **200** of the present preferred embodiment, as in the first preferred embodiment, because the pitches of the electrode fingers of the narrow pitch electrode finger portions are different, a spurious response in a band higher than the pass band is suppressed.

[0076] FIG. 5 is a schematic plan view that shows the electrode structure of a boundary acoustic wave filter device according to a third preferred embodiment of the present invention.

[0077] In the longitudinally coupled resonator boundary acoustic wave filter device **300** according to a third preferred embodiment of the present invention, a five-IDT type longitudinally coupled resonator boundary acoustic wave filter portion **310** is connected to the unbalanced terminal **106**. That is, the longitudinally coupled resonator boundary acoustic wave filter portion **310** includes a first IDT **314** that is arranged in the middle in boundary acoustic wave propagating direction. The IDT **314** includes first and second divided IDT portions **314a** and **314b** that are separately formed in the boundary acoustic wave propagating direction by dividing one of the bus bars of the IDT **314**. Second and third IDTs **313** and **315** are arranged on both sides of the IDT **314** in the boundary acoustic wave propagating direction. Fourth and fifth IDTs **312** and **316** are arranged on both sides of the region in which the IDTs **313** to **315** are provided in the boundary acoustic wave propagating direction. Reflectors **311** and **317** are arranged on both side of the region in which the IDTs **312** to **316** are arranged in the boundary acoustic wave propagating direction. Here, a one-port boundary acoustic wave resonator **320** is connected between the unbalanced terminal **106** and a ground. In addition, ends of the second and third IDTs **313** and **315** of the longitudinally coupled resonator boundary acoustic wave filter portion **310** are commonly electrically connected to the unbalanced terminal **106**. The other ends of the IDTs **313** and **315** are connected to a ground.

[0078] One end of the fourth IDT **312** and the divided IDT portion **314a** are commonly connected to the first balanced terminal **107** via a one-port boundary acoustic wave resonator **330**. The other end of the IDT **312** is connected to a ground. In addition, the second divided IDT portion **314b** and one end of the fifth IDT **316** are commonly electrically connected to the second balanced terminal **108** via a one-port boundary acoustic wave resonator **340**. In addition, the other end of the IDT **316** is connected to a ground. In addition, a common bus bar side of the IDT **314** is connected to a ground.

[0079] In the boundary acoustic wave filter device **300** of the present preferred embodiment, at the portion at which the IDTs **312** to **316** are arranged, narrow pitch electrode finger portions **312A**, **313A**, **313B**, **314A**, **314B**, **315A**, **315B** and **316A** are respectively provided at portions at which IDTs are located adjacent to each other. Thus, balancing is improved.

[0080] In addition, the pitch of the electrode fingers of each of the narrow pitch electrode finger portions **314A** and **314B** of the first IDT **314** is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions **313B** and **315A** of ends of the second and third IDTs **313** and **315**, adjacent to the IDT **314**. Thus, a spurious response is dispersed due to the narrow pitch electrode finger portions,

such that the magnitude of a spurious response in a band higher than the pass band is reduced.

[0081] In addition, the pitch of the electrode fingers of each of the narrow pitch electrode finger portions **312A** and **316A** of the fourth and fifth IDTs **312** and **316** is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions **313A** and **315B**. That is, the pitches of the electrode fingers of the narrow pitch electrode finger portions are varied between any adjacent portions at which IDTs are located adjacent to each other. As described above, all of the pitches of the electrode fingers of the narrow pitch electrode finger portions between any adjacent portions at which IDTs are located adjacent to each other are varied. Thus, a spurious response in a band higher than the pass band is effectively dispersed, such that the spurious response is further reduced.

[0082] Note that in the present preferred embodiment, in order to provide a balance-unbalance conversion function, the polarity of the IDT **315** is opposite to the polarity of the IDT **313**. However, in the five-IDT type longitudinally coupled resonator boundary acoustic wave filter, the polarity of each of a plurality of IDTs used to provide a balance-unbalance conversion function may be appropriately changed as long as the balance-unbalance converter function is provided.

[0083] For example, in a boundary acoustic wave filter device **400** according to an alternative example of a preferred embodiment of the present invention as shown in FIG. 6, a five-IDT type longitudinally coupled resonator boundary acoustic wave filter **410** is arranged between the unbalanced terminal **106** and the first and second balanced terminals **107** and **108**. Here, the longitudinally coupled resonator boundary acoustic wave filter portion **410** includes a first IDT **414**, second and third IDTs **413** and **415**, fourth and fifth IDTs **412** and **416**, and reflectors **411** and **417**. The first IDT **414** is arranged in the middle. The second and third IDTs **413** and **415** are arranged respectively on both sides of the first IDT **414** in the boundary acoustic wave propagating direction. The fourth and fifth IDTs **412** and **416** are arranged in the region in which the IDTs **413** to **415** are provided in the boundary acoustic wave propagating direction.

[0084] Then, one end of the first IDT **414** and ends of the fourth and fifth IDTs **412** and **416** are commonly connected to the unbalanced terminal **106** via a one-port boundary acoustic wave resonator **420**. A ground is connected to the other ends of the IDTs **412**, **414** and **416**. The polarity of the third IDT **415** is opposite to the polarity of the second IDT **413**. Then, ends of the IDTs **413** and **415** are connected to a ground, the other end of the IDT **413** is connected to the first balanced terminal **107**, and the other end of the third IDT **415** is connected to the second balanced terminal **108**. Note that a one-port boundary acoustic wave resonator **430** is preferably connected between the first and second balanced terminals **107** and **108**.

[0085] In the present alternative example, the polarity of the IDT **415** is opposite to the polarity of the IDT **413** such that the balance-unbalance converter function is provided.

[0086] In addition, in the present alternative example, narrow pitch electrode finger portions are provided at portions at which IDTs are located adjacent to each other, and the pitches of the electrode fingers of the narrow pitch electrode finger portions are varied between any adjacent portions. More specifically, the first IDT **414** includes narrow pitch electrode finger portions **414A** and **414B** located at both ends thereof. At a portion at which the first and second IDTs **413** and **414**

are located adjacent to each other, the pitch of the electrode fingers of the narrow pitch electrode finger portion 413B provided at an end of the IDT 413, adjacent to the IDT 414, is different from the pitch of the electrode fingers of the narrow pitch electrode finger portion 414A of the IDT 414. Similarly, between the narrow pitch electrode finger portion 412A provided in the IDT 412 and the narrow pitch electrode finger portion 413A of the IDT 413, the pitches of the electrode fingers are varied. In this manner, at the portion at which the narrow pitch electrode finger portions 412A and 413A are located adjacent to each other, at the portion at which the narrow pitch electrode finger portion 413B and the narrow pitch electrode finger portion 414A are located adjacent to each other, at the portion at which the narrow pitch electrode finger portion 414B and the narrow pitch electrode finger portion 415A are located adjacent to each other, and at the portion at which the narrow pitch electrode finger portion 415B and the narrow pitch electrode finger portion 416A are located adjacent to each other, the pitches of the electrode fingers of the adjacent narrow pitch electrode finger portions are varied. With this configuration, a spurious response is dispersed and reduced.

[0087] Note that in the preferred embodiments and alternative examples, the piezoelectric body is preferably made of LiNbO_3 having a principal plane obtained by rotating the Y-axis through about 15 degrees \pm 10 degrees. However, the piezoelectric body may be made of LiNbO_3 having another crystal angle. In addition, a piezoelectric body may be made of another piezoelectric material, such as LiTaO_3 or rock crystal, for example.

[0088] While preferred embodiments of the present invention have been described above, it is to be understood that variations and modifications will be apparent to those skilled in the art without departing the scope and spirit of the present invention. The scope of the present invention, therefore, is to be determined solely by the following claims.

What is claimed is:

1. A boundary acoustic wave filter device comprising:
 - a piezoelectric body;
 - a dielectric body laminated on the piezoelectric body; and
 - an electrode structure arranged at a boundary between the piezoelectric body and the dielectric body; wherein the boundary acoustic wave filter device utilizes an SH-type boundary acoustic wave that propagates along the boundary;
 - the electrode structure includes a first IDT, and second and third IDTs that are provided on both sides of the first IDT in a direction in which a boundary acoustic wave propagates to define a longitudinally coupled resonator boundary acoustic wave filter portion;
 - at portions of the first to third IDTs at which two IDTs are located adjacent to each other, a pitch of a portion of electrode fingers of one IDT located at an end adjacent to another IDT is less than a pitch of another portion of electrode fingers of the one IDT adjacent to that portion, so as to define a narrow pitch electrode finger portion; and
 - the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions provided in the first IDT and the second and third IDTs is different from the pitch of the electrode finger portions of each of the remaining narrow pitch electrode finger portions.
2. The boundary acoustic wave filter device according to claim 1, wherein the number of electrode fingers of each of

the narrow pitch electrode finger portions of the first IDT is different from the number of electrode fingers of each of the narrow pitch electrode finger portions of the second and third IDTs.

3. The boundary acoustic wave filter device according to claim 1, further comprising fourth and fifth IDTs, the fourth and fifth IDTs being arranged on both sides of the region in which the first to third IDTs are provided in the direction in which the boundary acoustic wave propagates, so as to define a five-IDT type longitudinally coupled resonator boundary acoustic wave filter portion.

4. A boundary acoustic wave filter device comprising:

- a piezoelectric body;
- a dielectric body laminated on the piezoelectric body; and
- an electrode structure arranged at a boundary between the piezoelectric body and the dielectric body; wherein the boundary acoustic wave filter device utilizes an SH-type boundary acoustic wave that propagates along the boundary;

the electrode structure includes first and second longitudinally coupled resonator filter portions, each of which includes a first IDT, and second and third IDTs that are arranged on both sides of the first IDT in a direction in which a boundary acoustic wave propagates;

at portions of the first to third IDTs at which two IDTs are located adjacent to each other, a pitch of a portion of electrode fingers of one IDT located at an end adjacent to another IDT is less than a pitch of another portion of electrode fingers of the one IDT adjacent to that portion, so as to define a narrow pitch electrode finger portion;

a polarity of each of the first to third IDTs of the first and second longitudinally coupled resonator boundary acoustic wave filter portions is set such that a phase of an output signal to an input signal of the second longitudinally coupled resonator boundary acoustic wave filter portion is different by about 180 degrees from a phase of an output signal to an input signal of the first longitudinally coupled resonator boundary acoustic wave filter portion;

an unbalanced terminal and first and second balanced terminals are provided, input ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are connected to the unbalanced terminal, and output ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are respectively connected to the first and second balanced terminals; and

the pitch of the electrode fingers of at least one of the narrow pitch electrode finger portions of the first IDT and the second and third IDTs is different from the pitch of the electrode finger portions of each of the remaining narrow pitch electrode finger portions.

5. The boundary acoustic wave filter device according to claim 4, wherein the number of electrode fingers of each of the narrow pitch electrode finger portions of the first IDT is different from the number of electrode fingers of each of the narrow pitch electrode finger portions of the second and third IDTs.

6. The boundary acoustic wave filter device according to claim 4, further comprising fourth and fifth IDTs, the fourth and fifth IDTs being arranged on both sides of the region in which the first to third IDTs are provided in the direction in

which the boundary acoustic wave propagates, so as to define a five-IDT type longitudinally coupled resonator boundary acoustic wave filter portion.

7. The boundary acoustic wave filter device according to claim 4, further comprising:

third and fifth longitudinally coupled resonator boundary acoustic wave filter portions that are configured the same or substantially the same as the first longitudinally coupled resonator boundary acoustic wave filter portion; and

fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions that are configured the same or substantially the same as the second longitudinally coupled resonator boundary acoustic wave filter portion; wherein

input ends of the first to sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the unbalanced terminal, output ends of the first, third and fifth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the first balanced terminal, and output ends of the second, fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the second balanced terminal.

8. A boundary acoustic wave filter device comprising:

a piezoelectric body;

a dielectric body laminated on the piezoelectric body; and an electrode structure arranged at a boundary between the piezoelectric body and the dielectric body; wherein the boundary acoustic wave filter device utilizes an SH-type boundary acoustic wave that propagates along the boundary;

the electrode structure includes first and second longitudinally coupled resonator filter portions, each of which includes a first IDT, and second and third IDTs that are arranged respectively on both sides of the first IDT in a direction in which a boundary acoustic wave propagates;

at portions of the first to third IDTs at which two IDTs are located adjacent to each other, a pitch of a portion of electrode fingers of one IDT located at an end adjacent to the other IDT is less than a pitch of another portion of electrode fingers of the one IDT, adjacent to that portion, so as to define a narrow pitch electrode finger portion;

a polarity of each of the first to third IDTs of the first and second longitudinally coupled resonator boundary acoustic wave filter portions is set such that a phase of an output signal to an input signal of the second longitudinally coupled resonator boundary acoustic wave filter portion is different by about 180 degrees from a phase of an output signal to an input signal of the first longitudinally coupled resonator boundary acoustic wave filter portion;

an unbalanced terminal and first and second balanced terminals are provided, input ends of the first and second longitudinally coupled resonator boundary acoustic

wave filter portions are connected to the unbalanced terminal, and output ends of the first and second longitudinally coupled resonator boundary acoustic wave filter portions are respectively connected to the first and second balanced terminals;

the pitches of the electrode fingers of the narrow pitch electrode finger portions of the first to third IDTs in the first longitudinally coupled resonator filter portion are equal or substantially equal to one another;

the pitches of the electrode fingers of the narrow pitch electrode finger portions of the first to third IDTs in the second longitudinally coupled resonator filter portion are equal or substantially equal to one another; and

the pitch of the electrode fingers of each of the narrow pitch electrode finger portions of the first to third IDTs in the first longitudinally coupled resonator filter portion is different from the pitch of the electrode fingers of each of the narrow pitch electrode finger portions of the first to third IDTs in the second longitudinally coupled resonator filter portion.

9. The boundary acoustic wave filter device according to claim 8, further comprising:

third and fifth longitudinally coupled resonator boundary acoustic wave filter portions that are configured the same or substantially the same as the first longitudinally coupled resonator boundary acoustic wave filter portion; and

fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions that are configured the same or substantially the same as the second longitudinally coupled resonator boundary acoustic wave filter portion; wherein

input ends of the first to sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the unbalanced terminal, output ends of the first, third and fifth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the first balanced terminal, and output ends of the second, fourth and sixth longitudinally coupled resonator boundary acoustic wave filter portions are connected to the second balanced terminal.

10. The boundary acoustic wave filter device according to claim 9, wherein the number of electrode fingers of each of the narrow pitch electrode finger portions of the first IDT is different from the number of electrode fingers of each of the narrow pitch electrode finger portions of the second and third IDTs.

11. The boundary acoustic wave filter device according to claim 8, further comprising fourth and fifth IDTs, the fourth and fifth IDTs being arranged on both sides of the region in which the first to third IDTs are provided in the direction in which the boundary acoustic wave propagates, so as to define a five-IDT type longitudinally coupled resonator boundary acoustic wave filter portion.

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